

MICRO ELECTRON

2SA928
PNP
SILICON
TRANSISTOR

DESCRIPTION

2SA928 is PNP silicon planar transistor dedesigned for audio power amplifier.

TO-92B



ECB

ABSOLUTE MAXIMUM RATINGS

| | | |
|--|----------|---------------|
| Collector-Base Voltage | VCBO | 30V |
| Collector-Emitter Voltage | VCEO | 30V |
| Emitter-Base Voltage | VEBO | 5V |
| Collector Current | IC | 2A |
| Continuous Power Dissipation | Pd | 1W |
| Operating & Storage Junction Temperature | Tj, Tstg | -55 to +150°C |

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNIT | CONDITIONS |
|--------------------------------------|----------|-----|-----|-----|------|------------------|
| Collector-Base Breakdown Voltage | BVCBO | 30 | | | | IC=100μA IE=0 |
| Collector-Emitter Breakdown Voltage | BVCEO | 30 | | | V | IC=10mA IB=0 |
| Emitter-Base Breakdown Voltage | BVEBO | 5 | | | V | IE=1mA IC=0 |
| Collector Cutoff Current | ICBO | | | 100 | nA | VCB=30V IE=0 |
| Emitter Cutoff Current | IEBO | | | 100 | nA | VEB=5V IC=0 |
| D.C. Current Gain | HFE | 100 | | 320 | | IC=500mA VCE=2V |
| | GROUP -O | 100 | | 200 | | IC=500mA VCE=2V |
| | GORUP -Y | 160 | | 320 | | IC=500mA VCE=2V |
| Base-Emitter Voltage | VBE | | | 1.0 | V | IC=500mA VCE=2V |
| Collector-Emitter Saturation Voltage | VCE(sat) | | | 2.0 | V | IC=1.5A IB=0.03A |
| Output Capacitance | Cob | | 48 | | pF | VCB=10V f=1MHz |
| Current Gain Bandwidth Product | ft | | 120 | | MHz | IC=500mA VCE=2V |



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